NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TPV695A** is a high gain push-pull device Designed for high power, band IV & V Transposers and transmitter amplifiers Applications.

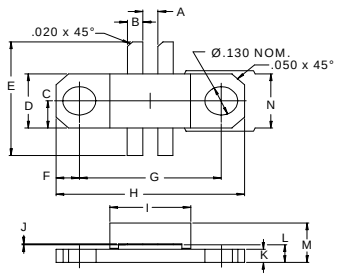
FEATURES:

- Gold Metalization
- Emitter Ballast Resistors
- Internal Input Matching

MAXIMUM RATINGS

I_C	5.0 A
V_{CE}	28 V
P_{DISS}	70 W @ T_C = 25 °C
T_J	-50 °C to +200 °C
T_{STG}	-50 °C to +200 °C
θ_{JC}	2.5 °C/W

PACKAGE STYLE .250 BAL FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.060 / 1.52	
B	.055 / 1.40	.065 / 1.65
C	.125 / 3.18	
D	.243 / 6.17	.255 / 6.48
E	.630 / 16.00	.670 / 17.01
F	.092 / 2.34	
G	.555 / 14.10	.565 / 14.35
H	.739 / 18.77	.750 / 19.05
I	.315 / 8.00	.327 / 8.31
J	.002 / 0.05	.006 / 0.15
K	.055 / 1.40	.065 / 1.65
L	.075 1.91	.095 / 2.41
M		.190 / 4.83
N	.245 / 6.22	.257 / 6.53

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 40 mA	28			V
BV_{CBO}	I_C = 20 mA	45			V
BV_{EBO}	I_E = 5.0 mA	3.0			V
I_{CBO}	V_{CB} = 20 V			15	mA
h_{FE}	I_C = 500 mA V_{CE} = 20 V	20		80	---
C_{OB}	V_{CB} = 25 V f = 1.0 MHz			20	pF
P_G IMD_3	V_{CE} = 25 V P_{OUT} = 14 W f = 845 MHz	8.5	-47		dB dBc